

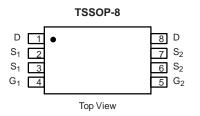
AP9928GEO-VB Datasheet Dual N-Channel 25-V (D-S) MOSFET

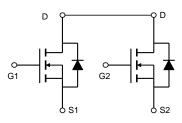
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
25	0.022 at V _{GS} = 4.5 V	6.6		
20	0.032 at V _{GS} = 2.5 V	5.5		

FEATURES

- Halogen-free Option Available
- Trench Power MOSFETs







ABSOLUTE MAXIMUM RATINGS	$_{A} = 25 \ ^{\circ}C, \ unles$	s otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	25		V
Gate-Source Voltage		V _{GS}	± 12		v
Continuous Drain Current /T 450 %0\3	T _A = 25 °C	– I _D	6.6	5.2	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		5.5	3.5	
Pulsed Drain Current		I _{DM}	30		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.5	1.0	
	T _A = 25 °C	- P _D	1.5	1.0	w
Maximum Power Dissipation ^a	T _A = 70 °C		0.96	0.64	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Maximum has the Archiveta	t ≤ 10 s	- R _{thJA}	72	83	
Maximum Junction-to-Ambient ^a	Steady State		100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	55	70	

Notes:

a. Surface Mounted on FR4 board, $t \leq 10 \mbox{ s.}$

* Pb containing terminations are not RoHS compliant, exemptions may apply.

Parameter	Symbol	Min.	Tup a	Max.	Unit		
	Symbol	Test Conditions	wiin.	Typ. ^a	widx.	Unit	
Static	1		-				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.5		1.0	V	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 4.5 V			± 200	nA	
Zara Cata Valtaga Drain Current	I _{DSS}	$V_{DS} = 25 V, V_{GS} = 0 V$			1		
Zero Gate Voltage Drain Current		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			25	μΑ	
On-State Drain Current ^b	I _{D(on)}	$V_{DS}{\leq}5$ V, V_{GS} = 4.5 V	30			А	
Drain-Source On-State Resistance ^b	D	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$		0.022			
	R _{DS(on)}	V_{GS} = 2.5 V, I _D = 5.5 A		0.032		Ω	
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V _{SD}	$I_{S} = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Qg			12	18		
Gate-Source Charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 6.5 A		2.2		nC	
Gate-Drain Charge	Q _{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong \text{1}$ A, V_GEN = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765]	

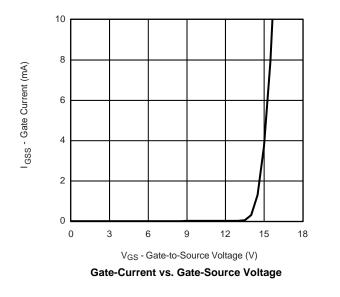
Notes:

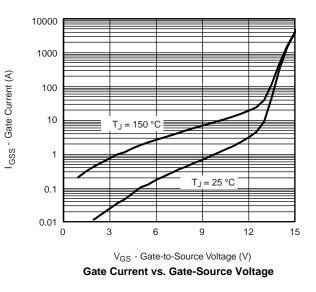
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



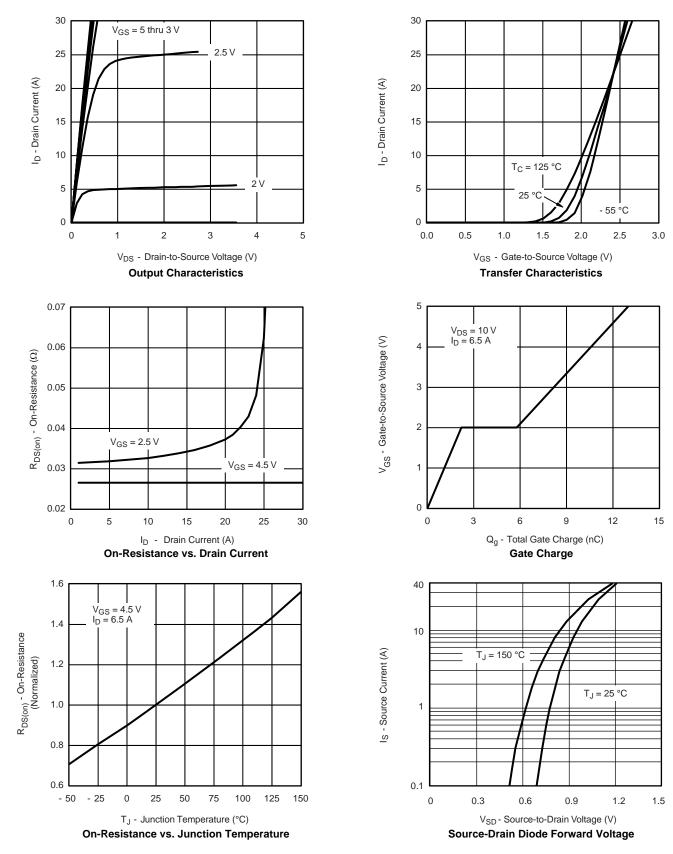


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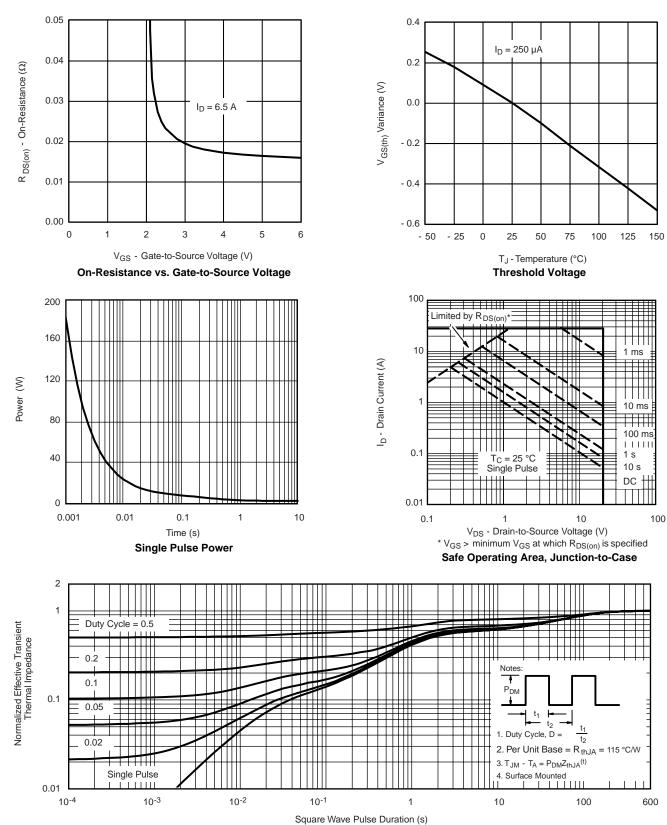
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







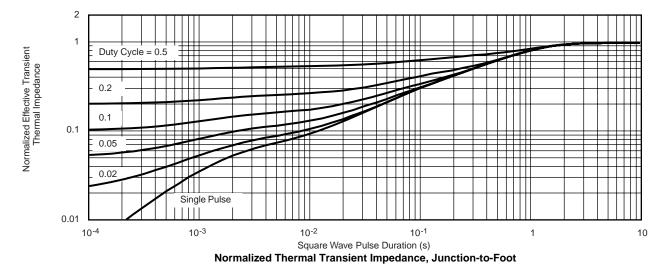
Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

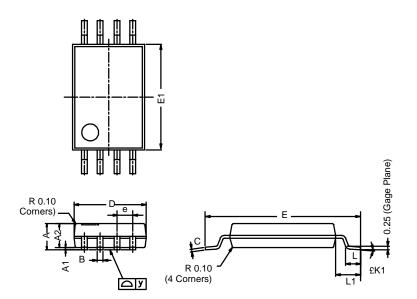


AP9928GEO-VB



TSSOP: 8-LEAD

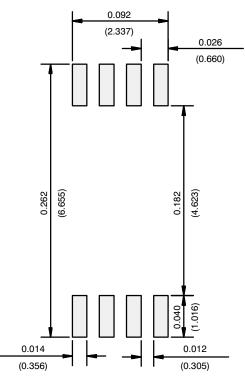
JEDEC Part Number: MO-153



	MILLIMETERS				
Dim	Min	Nom M			
Α	-	-	1.20		
A ₁	0.05	0.10	0.15		
A ₂	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
E	6.20	6.40	6.60		
E ₁	4.30	4.40	4.50		
е	-	0.65	-		
L	0.45	0.60	0.75		
L ₁	0.90	1.00	1.10		
Y	-	-	0.10		
£ K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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